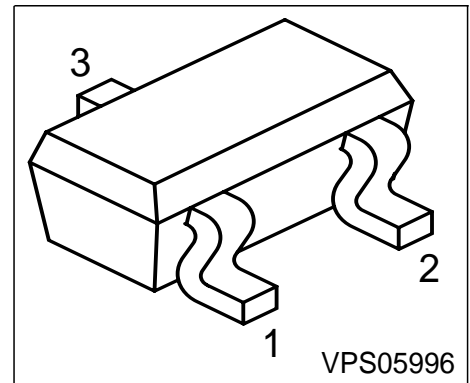


**NPN Silicon RF Transistor**
**Preliminary data**

- For broadband amplifiers up to 2 GHz and fast non-saturated switches at collector currents from 0.5 mA to 20 mA
- Complementary type: BFT92T (PNP)



**ESD:** Electrostatic discharge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration			Package
BFR92T	GFs	1 = B	2 = E	3 = C	SC75

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CEO}$	15	V
Collector-emitter voltage	$V_{CES}$	20	
Collector-base voltage	$V_{CBO}$	20	
Emitter-base voltage	$V_{EBO}$	2.5	
Collector current	$I_C$	30	mA
Base current	$I_B$	4	
Total power dissipation $T_S \leq 69^\circ\text{C}^1$	$P_{tot}$	280	mW
Junction temperature	$T_j$	150	°C
Ambient temperature	$T_A$	-65 ... 150	
Storage temperature	$T_{stg}$	-65 ... 150	

**Thermal Resistance**

Junction - soldering point <sup>2)</sup>	$R_{thJS}$	$\leq 290$	K/W
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<sup>1</sup>  $T_S$  is measured on the collector lead at the soldering point to the pcb

<sup>2</sup> For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>DC characteristics</b>					
Collector-emitter breakdown voltage $I_C = 1 \text{ mA}, I_B = 0$	$V_{(BR)CEO}$	15	-	-	V
Collector-emitter cutoff current $V_{CE} = 20 \text{ V}, V_{BE} = 0$	$I_{CES}$	-	-	10	$\mu\text{A}$
Collector-base cutoff current $V_{CB} = 10 \text{ V}, I_E = 0$	$I_{CBO}$	-	-	100	nA
Emitter-base cutoff current $V_{EB} = 2.5 \text{ V}, I_C = 0$	$I_{EBO}$	-	-	100	$\mu\text{A}$
DC current gain $I_C = 15 \text{ mA}, V_{CE} = 8 \text{ V}$	$h_{FE}$	40	100	200	-

**Electrical Characteristics** at  $T_A = 25^\circ\text{C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC characteristics</b> (verified by random sampling)					
Transition frequency $I_C = 15 \text{ mA}$ , $V_{CE} = 8 \text{ V}$ , $f = 500 \text{ MHz}$	$f_T$	3.5	5	-	GHz
Collector-base capacitance $V_{CB} = 10 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{cb}$	-	0.38	0.6	pF
Collector-emitter capacitance $V_{CE} = 10 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{ce}$	-	0.2	-	
Emitter-base capacitance $V_{EB} = 0.5 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{eb}$	-	0.7	-	
Noise figure $I_C = 2 \text{ mA}$ , $V_{CE} = 6 \text{ V}$ , $Z_S = Z_{Sopt}$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$F$	-	1.8 2.9	-	dB
Power gain, maximum available <sup>1)</sup> $I_C = 15 \text{ mA}$ , $V_{CE} = 8 \text{ V}$ , $Z_S = Z_{Sopt}$ , $Z_L = Z_{Lopt}$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$G_{ma}$	-	16 10.5	-	
Transducer gain $I_C = 15 \text{ mA}$ , $V_{CE} = 8 \text{ V}$ , $Z_S = Z_L = 50\Omega$ , $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$	$ S_{21e} ^2$	-	13.5 8	-	

$$^1G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$$

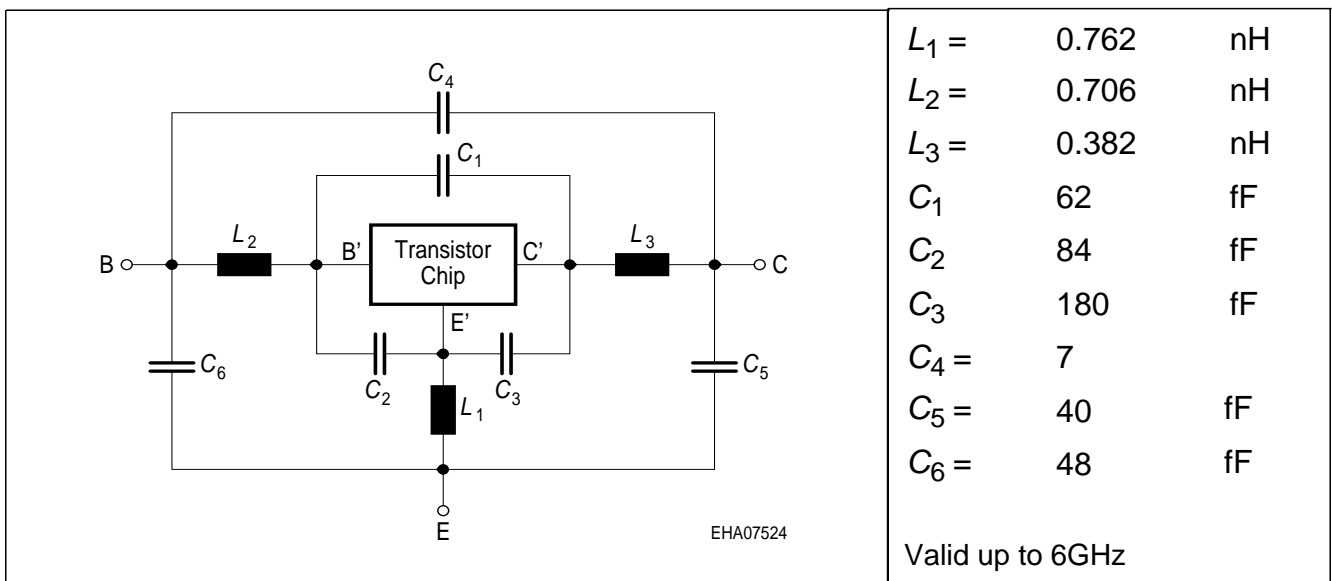
**SPICE Parameters (Gummel-Poon Model, Berkley-SPICE 2G.6 Syntax) :**

**Transistor Chip Data**

IS =	0.1213	fA	BF =	94.733	-	NF =	1.0947	-
VAF =	30	V	IKF =	0.46227	A	ISE =	129.55	fA
NE =	1.9052	-	BR =	10.729	-	NR =	0.8983	-
VAR =	14.599	V	IKR =	0.01	A	ISC =	0.75557	fA
NC =	1.371	-	RB =	14.998	$\Omega$	IRB =	0.01652	mA
RBM =	7.8145	$\Omega$	RE =	0.29088	$\Omega$	RC =	0.13793	$\Omega$
CJE =	10.416	fF	VJE =	0.70618	V	MJE =	0.34686	-
TF =	26.796	ps	XTF =	0.3817	-	VTF =	0.32861	V
ITF =	4.4601	mA	PTF =	0	deg	CJC =	946.47	fF
VJC =	0.84079	V	MJC =	0.4085	-	XCJC =	0.13464	-
TR =	1.2744	ns	CJS =	0	fF	VJS =	0.75	V
MJS =	0	-	XTB =	0	-	EG =	1.11	eV
XTI =	3	-	FC =	0.99545	-	TNOM	300	K

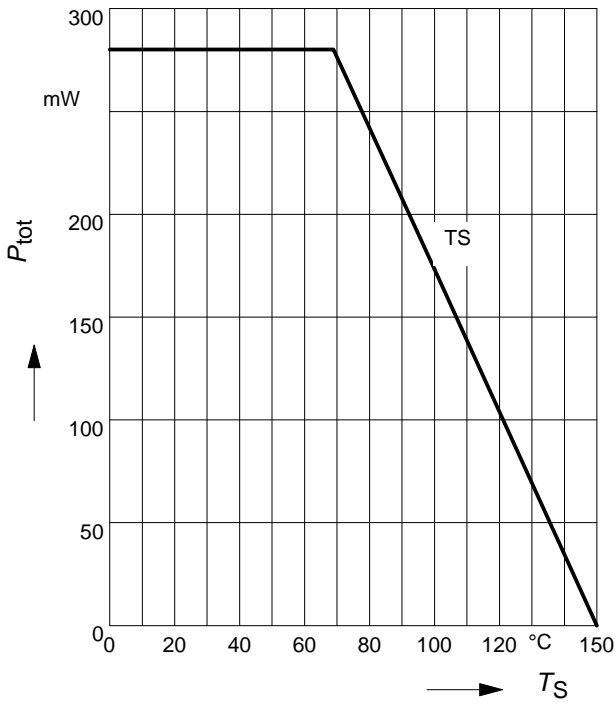
All parameters are ready to use, no scaling is necessary.  
 Extracted on behalf of Infineon Technologies AG by:  
 Institut für Mobil-und Satellitentechnik (IMST)

**Package Equivalent Circuit:**

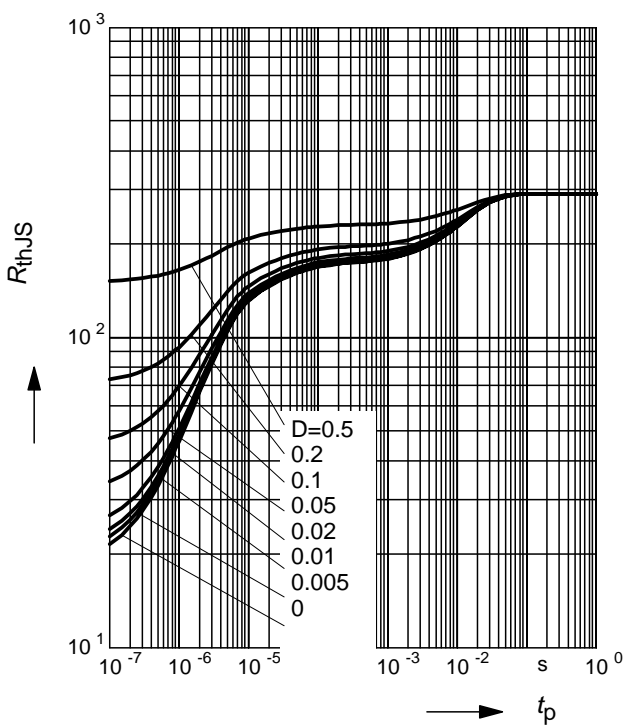


For examples and ready to use parameters please contact your local Infineon Technologies distributor or sales office to obtain a Infineon Technologies CD-ROM or see Internet: <http://www.infineon.com/silicondiscretes>

**Total power dissipation  $P_{tot} = f(T_S)$**

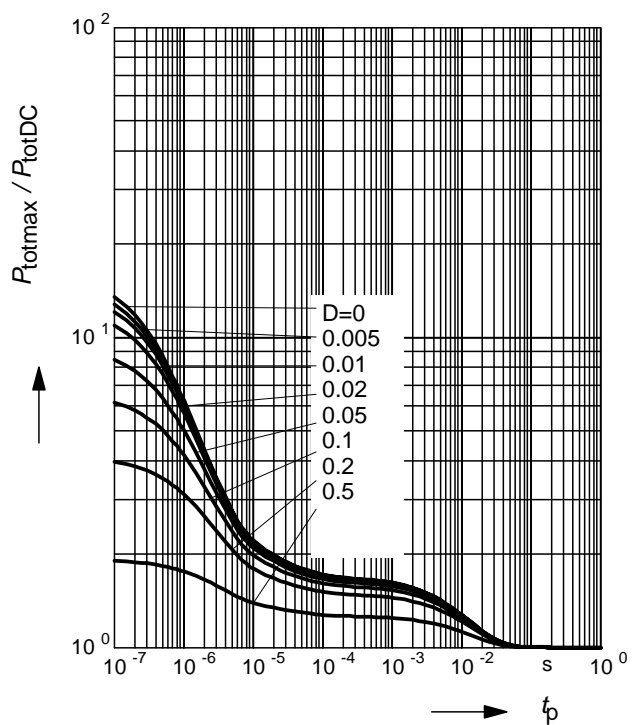


**Permissible Pulse Load  $R_{thJS} = f(t_p)$**



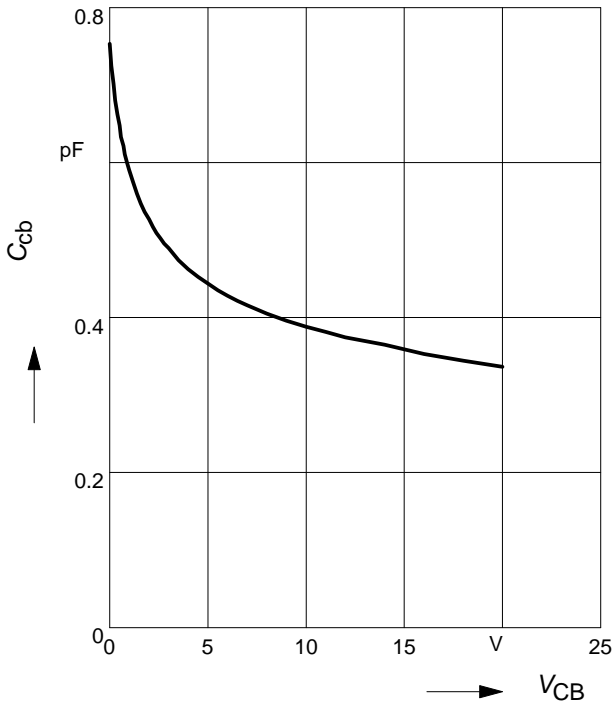
**Permissible Pulse Load**

$P_{totmax}/P_{totDC} = f(t_p)$



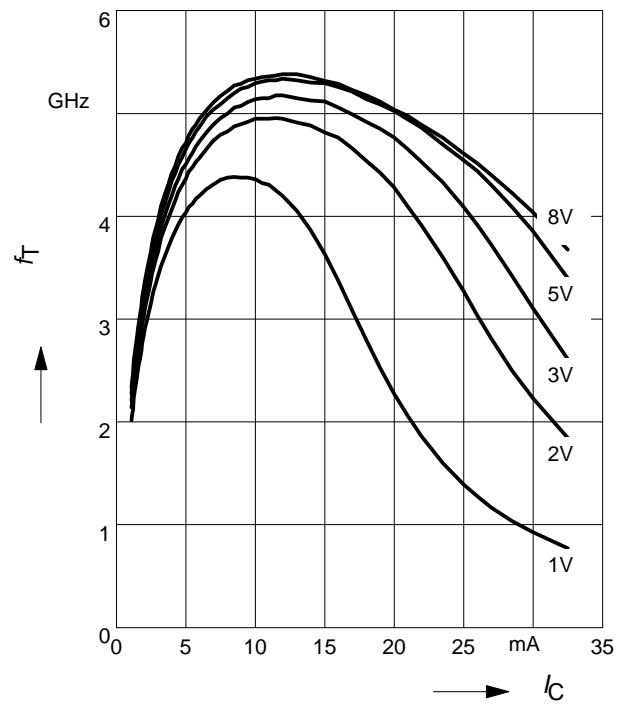
**Collector-base capacitance  $C_{cb} = f(V_{CB})$**

$f = 1\text{MHz}$



**Transition frequency  $f_T = f(I_C)$**

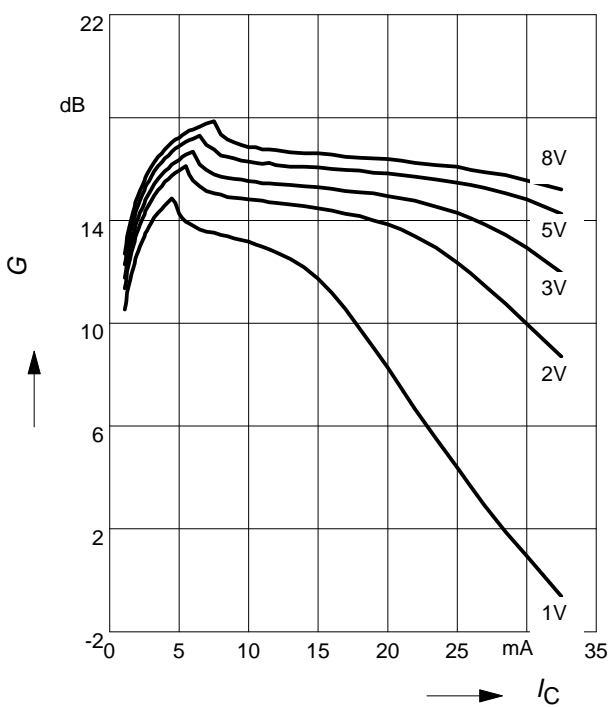
$V_{CE} = \text{Parameter}$



**Power Gain  $G_{ma}, G_{ms} = f(I_C)$**

$f = 0.9\text{GHz}$

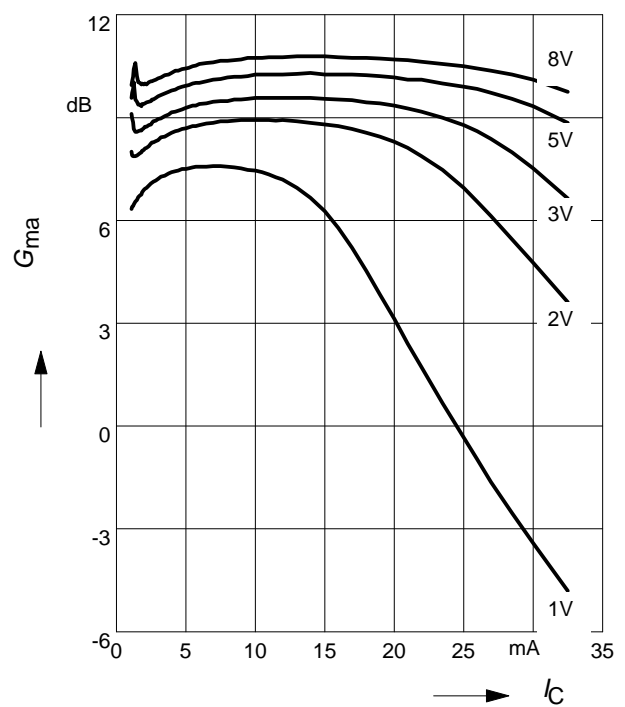
$V_{CE} = \text{Parameter}$



**Power Gain  $G_{ma}, G_{ms} = f(I_C)$**

$f = 1.8\text{GHz}$

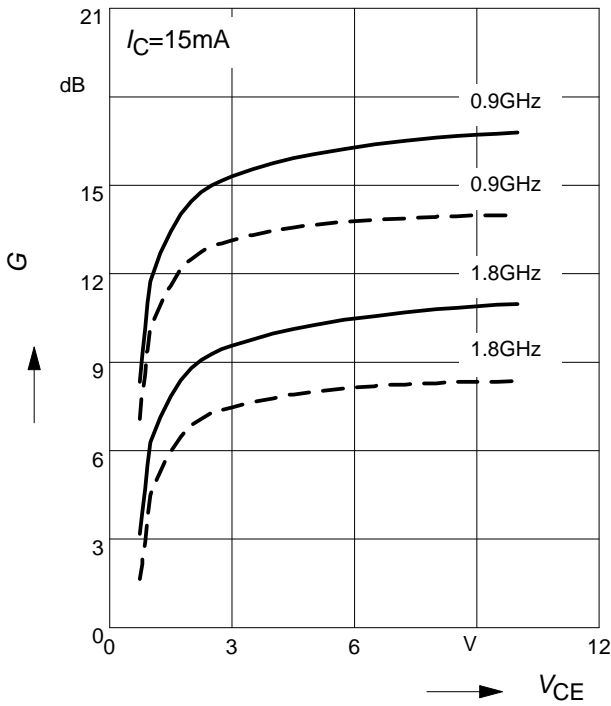
$V_{CE} = \text{Parameter}$



**Power Gain**  $G_{ma}, G_{ms} = f(V_{CE})$ : \_\_\_\_\_

$|S_{21}|^2 = f(V_{CE})$ : - - - - -

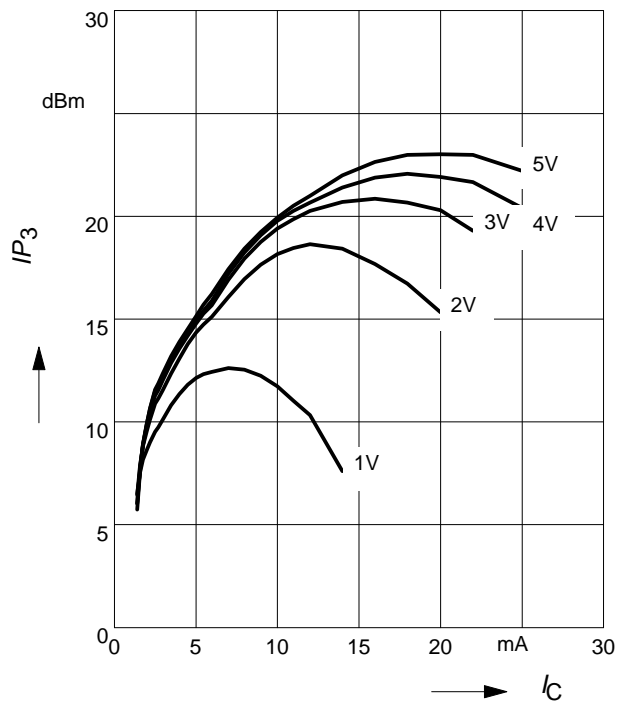
$f =$  Parameter



**Intermodulation Intercept Point**  $IP_3 = f(I_C)$

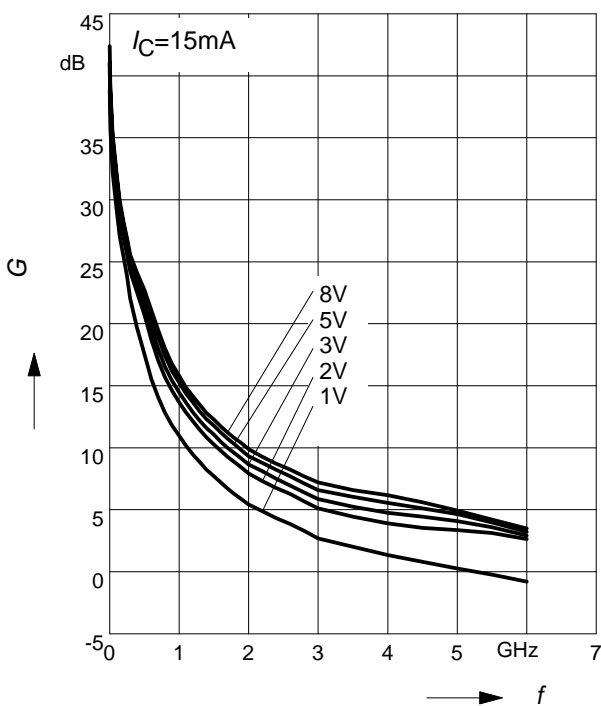
(3rd order, Output,  $Z_S = Z_L = 50\Omega$ )

$V_{CE} =$  Parameter,  $f = 900\text{MHz}$



**Power Gain**  $G_{ma}, G_{ms} = f(f)$

$V_{CE} =$  Parameter



**Power Gain**  $|S_{21}|^2 = f(f)$

$V_{CE} =$  Parameter

